

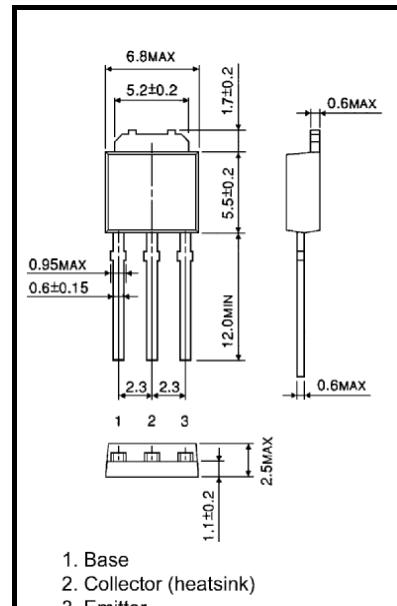
Strobe Flash Applications
Medium Power Amplifier Applications

Unit: mm

- Excellent hFE linearity
 - : hFE (1) = 100 to 320 (VCE = -2 V, IC = -0.5 A)
 - : hFE (2) = 70 (min) (VCE = -2 V, IC = -4 A)
- Low collector saturation voltage
 - : VCE (sat) = -1.0 V (max) (IC = -4 A, IB = -0.1 A)
- High power dissipation
 - : PC = 10 W (Tc = 25°C), PC = 1.0 W (Ta = 25°C)

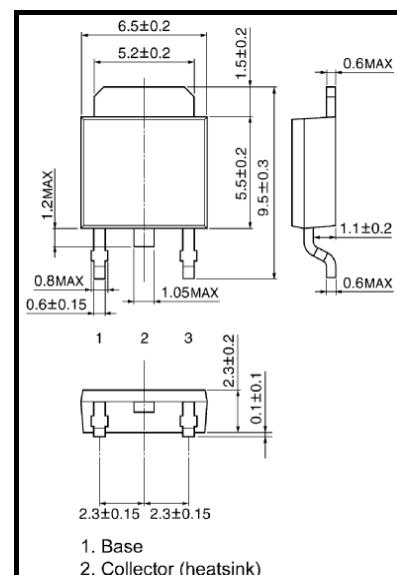
Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Collector-base voltage		V _{CBO}	-35	V
Collector-emitter voltage		V _{CEO}	-20	V
Emitter-base voltage		V _{EBO}	-8	V
Collector current	DC	I _C	-5	A
	Pulsed (Note 1)	I _{CP}	-8	
Base current		I _B	-0.5	A
Collector power dissipation	T _a = 25°C	P _C	1.0	W
	T _c = 25°C		10	
Junction temperature		T _j	150	°C
Storage temperature range		T _{stg}	-55 to 150	°C


 1. Base
 2. Collector (heatsink)
 3. Emitter

JEDEC	—
JEITA	—
TOSHIBA	2-7B1A

Weight: 0.36 g (typ.)


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Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = -35\text{ V}, I_E = 0$	—	—	-100	nA
Emitter cut-off current	I_{EBO}	$V_{EB} = -8\text{ V}, I_C = 0$	—	—	-100	nA
Collector-emitter breakdown voltage	V_{CEO}	$I_C = -10\text{ mA}, I_B = 0$	-20	—	—	V
Emitter-base breakdown voltage	V_{EBO}	$I_E = -1\text{ mA}, I_C = 0$	-8	—	—	V
DC current gain	h_{FE} (1) (Note 3)	$V_{CE} = -2\text{ V}, I_C = -0.5\text{ A}$	100	—	320	
	h_{FE} (2)	$V_{CE} = -2\text{ V}, I_C = -4\text{ A}$	70	—	—	
Collector-emitter saturation voltage	$V_{CE(\text{sat})}$	$I_C = -4\text{ A}, I_B = -0.1\text{ A}$	—	—	-1.0	V
Base-emitter voltage	V_{BE}	$V_{CE} = -2\text{ V}, I_C = -4\text{ A}$	—	—	-1.5	V
Transition frequency	f_T	$V_{CE} = -2\text{ V}, I_C = -0.5\text{ A}$	—	170	—	MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	62	—	pF

Marking

